

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,835,111 B2  
APPLICATION NO. : 09/994511  
DATED : December 28, 2004  
INVENTOR(S) : Kie Y. Ahn and Leonard Forbes

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

	<u>Reads</u>	<u>Should Read</u>
On Title Page Item (56), References Cited, Litovchenko	"IEEE International Conf. On Plasma Science,"	--IEEE International Conf. on Plasma Science,--
On Title Page Item (56), References Cited, Vaudaine	"technical digest of IEDM 91,"	--Technical Digest of IEDM 91,--
Column 1, Line 11	"displays, and,"	--displays and,--
Column 3, Line 52	"n-type Silicon"	--N-Type Silicon--
Column 3, Line 55	"increasing ND"	--increasing N <sub>D</sub> --
Column 4, Line 24	"IEEE E1."	--IEEE E1.--
Column 5, Line 5	"limiting, and"	--limiting and--
Column 6, Line 16	"from a normal"	--from normal--
Column 6, Line 31	"Mechanisms In"	--Mechanisms in--
Column 6, Line 39	"the ITO-P Inter SiO Intermediate Layer"	--the ITO-P Interface in $\alpha$ -Si:H Solar Cells Using a Thin SiO Intermediate Layer"--
Column 7, Line 20	"69(7), (1996), pp. 916- 918."	--69(7) (1996), pp. 916- 918.--
Column 7, Line 35	"Silicon at low"	--Silicon at Low--
Column 7, Line 57	"emitters 30', in a step"	--emitters 30' in a step--
Column 9, Line 63	"forms porous silicon"	--forms a porous silicon--
Column 10, Line 8	"A method of claim 19"	--The method of claim 19--

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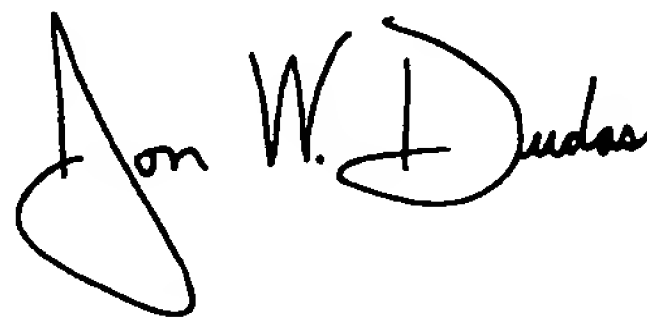
Page 2 of 2

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	<u>Reads</u>	<u>Should Read</u>
Column 10, Line 26	"wherein the act or forming"	--wherein the act of forming--
Column 10, Line 34	"Tie method of claim 22"	--The method of claim 22--
Column 10, Line 42	"Tho method of claim 22"	--The method of claim 22--
Column 10, Line 44	"layer at temperature"	--layer at a temperature--

Signed and Sealed this

Seventeenth Day of October, 2006



JON W. DUDAS  
*Director of the United States Patent and Trademark Office*